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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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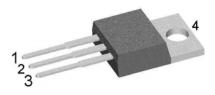
Schottky Diode Gen²

 V_{RRM} = 150 V I_{FAV} = 2x 30 A V_{F} = 0.8 V

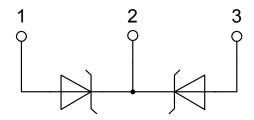
High Performance Schottky Diode Low Loss and Soft Recovery Common Cathode

Part number

DSA60C150PB



Backside: cathode



Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

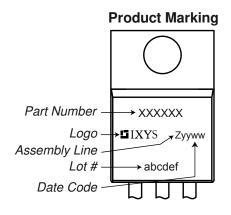




Schottky					Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ing voltage	$T_{VJ} = 25^{\circ}C$			150	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			150	V
I _R	reverse current, drain current	V _R = 150 V	$T_{VJ} = 25^{\circ}C$			450	μA
		$V_R = 150 V$	$T_{VJ} = 125^{\circ}C$			5	mΑ
V _F	forward voltage drop	I _F = 30 A	$T_{VJ} = 25^{\circ}C$			0.93	V
		$I_F = 60 \text{ A}$				1.09	V
		I _F = 30 A	T _{VJ} = 125°C			0.80	V
		$I_F = 60 \text{ A}$				0.98	V
I _{FAV}	average forward current	T _c = 150°C	T _{vJ} = 175°C			30	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		T _{vJ} = 175°C			0.55	V
r _F	slope resistance	oss calculation only				6	mΩ
R _{thJC}	thermal resistance junction to case	е				0.85	K/W
R _{thCH}	thermal resistance case to heatsin	nk			0.50		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			175	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			390	Α
C¹	junction capacitance	V _R = 12 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		289		pF



Package TO-220				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal 1)			35	Α	
T _{VJ}	virtual junction temperature		-55		175	°C	
T _{op}	operation temperature		-55		150	°C	
T _{stg}	storage temperature		-55		150	°C	
Weight				2		g	
M _D	mounting torque		0.4		0.6	Nm	
F _c	mounting force with clip		20		60	N	



Part number

D = Diode

S = Schottky Diode

A = low VF

60 = Current Rating [A] C = Common Cathode

150 = Reverse Voltage [V] PB = TO-220AB (3)

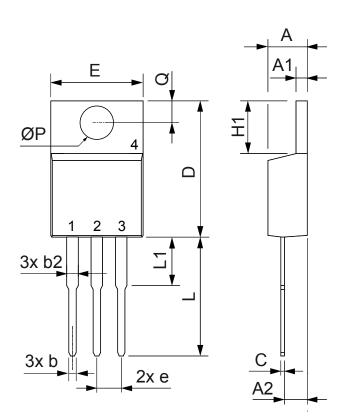
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA60C150PB	DSA60C150PB	Tube	50	509198

Similar Part	Package	Voltage class
DSA50C150HB	TO-247AD (3)	150

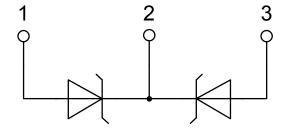
Equiva	alent Circuits for	Simulation	* on die level	T _{vJ} = 175 °C
$I \rightarrow V_0$	R_0	Schottky		
V _{0 max}	threshold voltage	0.55		V
R_{0max}	slope resistance *	2.8		mΩ



Outlines TO-220



Dim.	Millir	neter	Incl	Inches	
	Min.	Max.	Min.	Max.	
Α	4.32	4.82	0.170	0.190	
A1	1.14	1.39	0.045	0.055	
A2	2.29	2.79	0.090	0.110	
b	0.64	1.01	0.025	0.040	
b2	1.15	1.65	0.045	0.065	
С	0.35	0.56	0.014	0.022	
D	14.73	16.00	0.580	0.630	
Е	9.91	10.66	0.390	0.420	
е	2.54	BSC	0.100	BSC	
H1	5.85	6.85	0.230	0.270	
L	12.70	13.97	0.500	0.550	
L1	2.79	5.84	0.110	0.230	
ØP	3.54	4.08	0.139	0.161	
Q	2.54	3.18	0.100	0.125	





Schottky

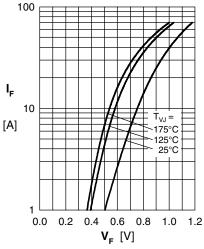


Fig. 1 Maximum forward voltage drop characteristics

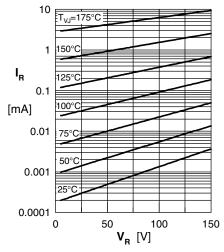


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

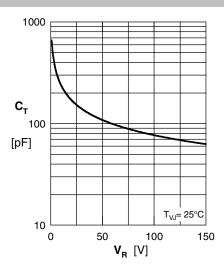


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

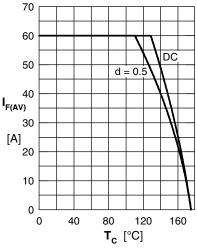


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temperature T_{C}

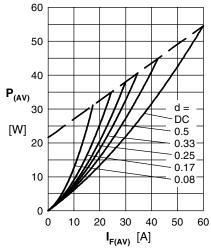


Fig. 5 Forward power loss characteristics

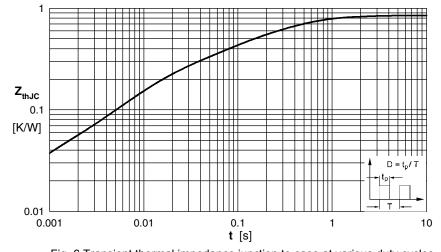


Fig. 6 Transient thermal impedance junction to case at various duty cycles

i	R _{thi} [K/W]	t _i [s]
1	0.02326	0.0005
2	0.1539	0.011
3	0.2031	0.072
4	0.3892	0.34
5	0.08053	1.5